Abstracts

Silicon RF-GCMOS IC technology for RF mixed-mode wireless applications (1997 Vol. I [MWSYM])

Jun Ma, Han-Bin Liang, D. Ngo, E. Spears, B. Yeung, B. Courson, D. Spooner, D. Lamey, J. Alvarez, T. Teraji, J. Ford and S. Cheng. "Silicon RF-GCMOS IC technology for RF mixed-mode wireless applications (1997 Vol. I [MWSYM])." 1997 MTT-S International Microwave Symposium Digest 1. (1997 Vol. I [MWSYM]): 123-127.

A submicron silicon Radio Frequency Graded-Channel MOS (RF-GCMOS) IC technology has been developed for wireless communication applications. The technology is based on a low power, low cost GCMOS VLSI technology with fully integrated passive components and optimized GC-MOSFETs for RF mixed-mode operations. For the first time, excellent RF and mixed-mode performance is demonstrated by the highly integrated RF GCMOS technology. The results show that this technology is most promising for battery-powered system-on-a-chip applications.

❑ Return to main document.